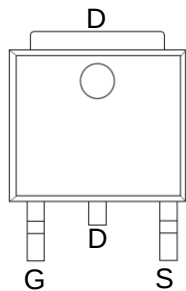


Features

- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application

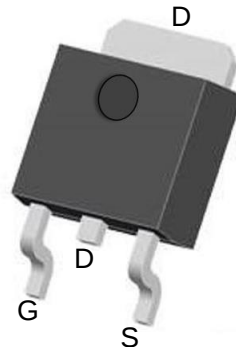


Marking and pin assignment

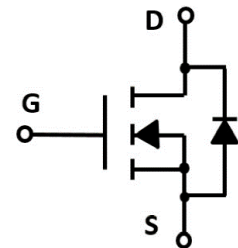
60V/30A N-Channel MOSFET

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
60V	30mΩ@10V	30A
	40mΩ@4.5V	



TO-252 top view



Schematic diagram



Pb-Free



RoHS



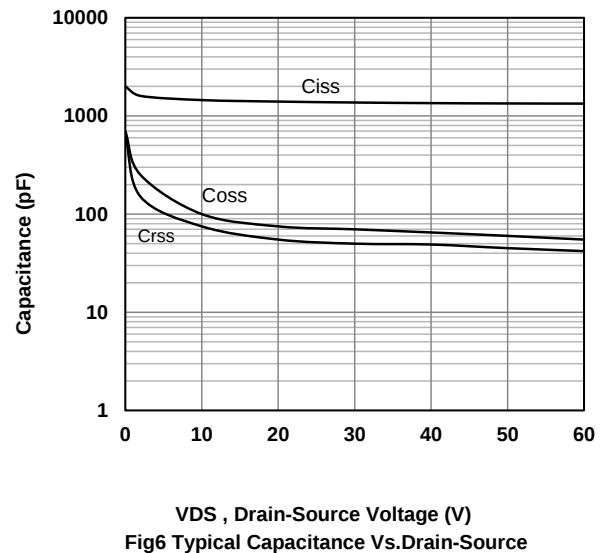
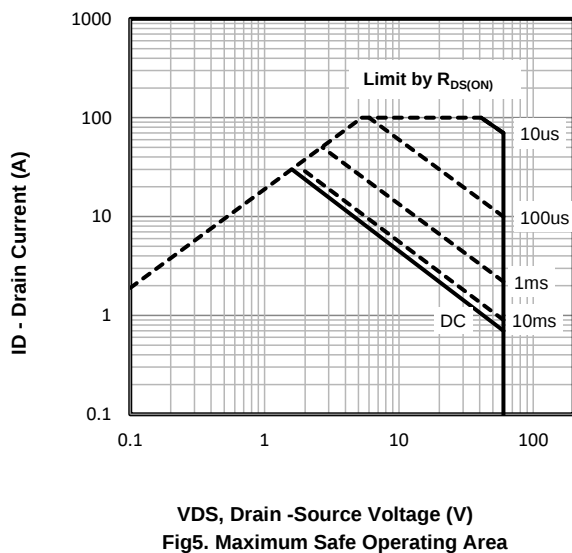
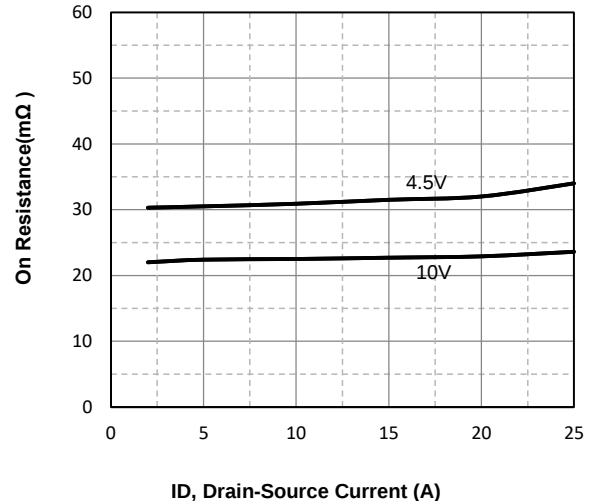
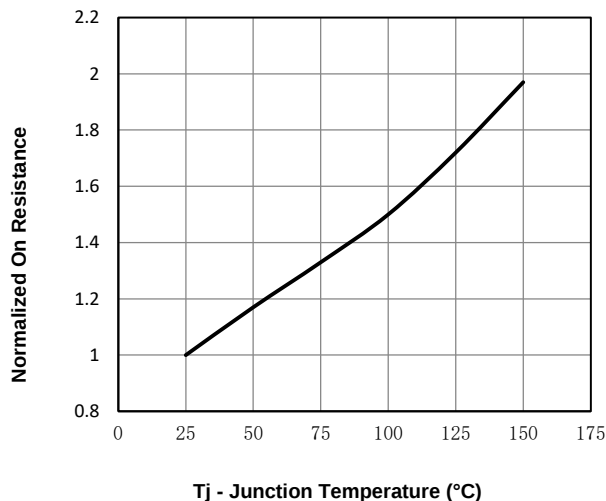
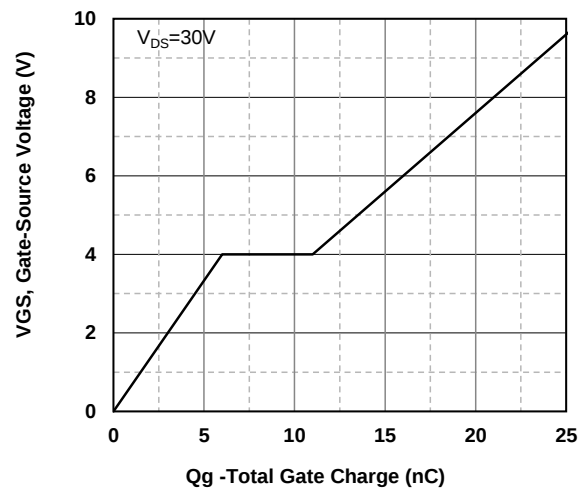
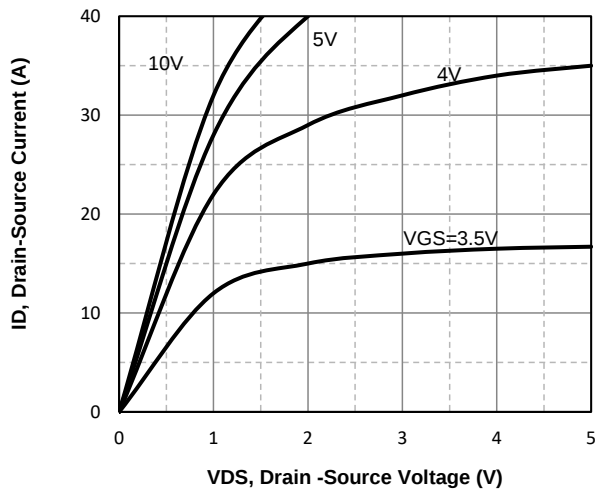
Halogen-Free

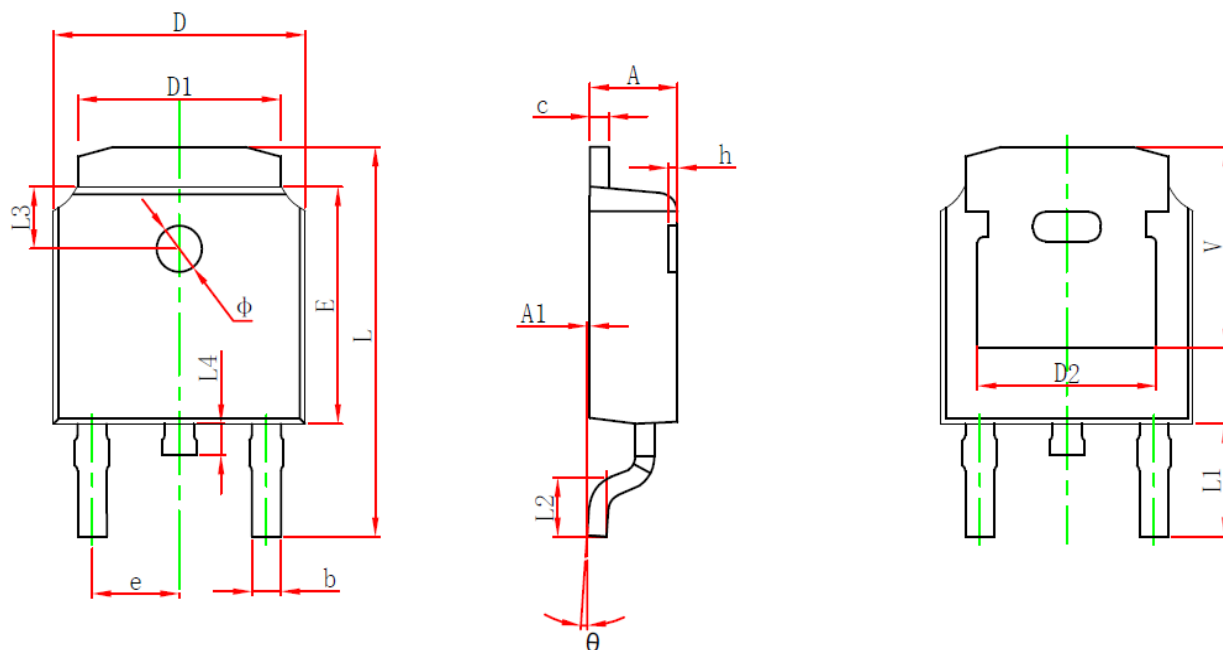
Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		60	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	30	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	100	A
I _D	Continuous Drain Current@GS=10V	Tc=25°C	30	A
P _D	Maximum Power Dissipation	Tc=25°C	41.5	W
E _{AS}	Single pulse avalanche energy ^{Note1}		48	mJ

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V, VGS=0V	--	--	1	uA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.2	1.7	2.5	V
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=10A	--	22	30	mΩ
		VGS=4.5V, ID=5A	--	30	40	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
CISS	Input Capacitance	VDS=30V, VGS=0V, f=1MHz	--	1050	--	pF
COSS	Output Capacitance		--	65	--	pF
CRSS	Reverse Transfer Capacitance		--	55	--	pF
Switching Characteristics						
Qg	Total Gate Charge	VDD=30V, ID=10A, VGS=10V	--	26	--	nC
Qgs	Gate Source Charge		--	5.7	--	nC
Qgd	Gate Drain Charge		--	5.2	--	nC
td(on)	Turn-on Delay Time	VDD=30V, ID=10A, VGS=10V, RG=3Ω	--	8.4	--	nS
tr	Turn-on Rise Time		--	8.5	--	nS
td(off)	Turn-Off Delay Time		--	36	--	nS
tf	Turn-Off Fall Time		--	5	--	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	Tj=25℃, Is=10A,	--	0.8	1.2	V

Note1:L=0.5mH, VDD=30V, Start T_J=25°C.

Typical Operating Characteristics



TO-252 Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.095
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.450	0.580	0.018	0.023
D	6.500	6.700	0.257	0.265
D1	5.100	5.460	0.202	0.216
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.237	0.245
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.384	0.408
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.040
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	